

**Amendments to the Claims:**

The listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1-14. (Cancelled).

15. (Currently Amendment) A semiconductor device, comprising:  
an embedded insulation layer formed in a semiconductor substrate;  
a plurality of power semiconductor ~~elements~~ transistors formed on said semiconductor substrate;  
a trench isolating between said plurality of power semiconductor ~~elements~~ transistors formed on said semiconductor substrate on said embedded insulation layer, whereby said plurality of semiconductor ~~element~~ transistors are individually isolated from each other and, isolated from any other semiconductor transistors;  
an isolator insulating and driving control electrodes of said power semiconductor elements; and  
wherein at least two of said plurality of power semiconductor ~~elements~~ transistors are each connected to ~~at least two different device terminals in order to provide connectability to said semiconductor device~~ each other in series.

16. (Previously Presented) A semiconductor device according to claim 15, wherein said plurality of power semiconductor ~~elements~~ transistors drive an ignition coil.

17. (Previously Presented) A semiconductor device according to claim 15, wherein said plurality of power semiconductor ~~elements~~ transistors drive a fuel injection valve.

18. (Previously Presented) A semiconductor device according to claim 15, wherein said plurality of power semiconductor ~~elements~~ transistors have an input control circuit supplying a control signal of a specific control pattern to said control electrodes of said plurality of power semiconductor ~~elements~~ transistors on the base of input signals.